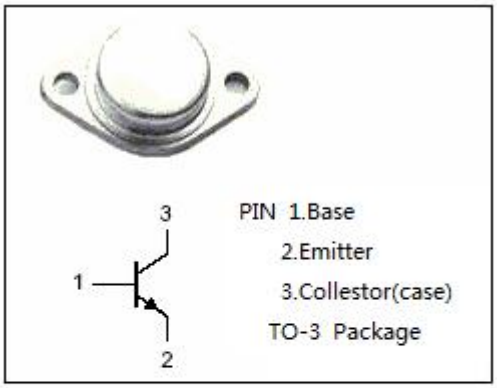
isc Silicon NPN Power Transistor 2SD764

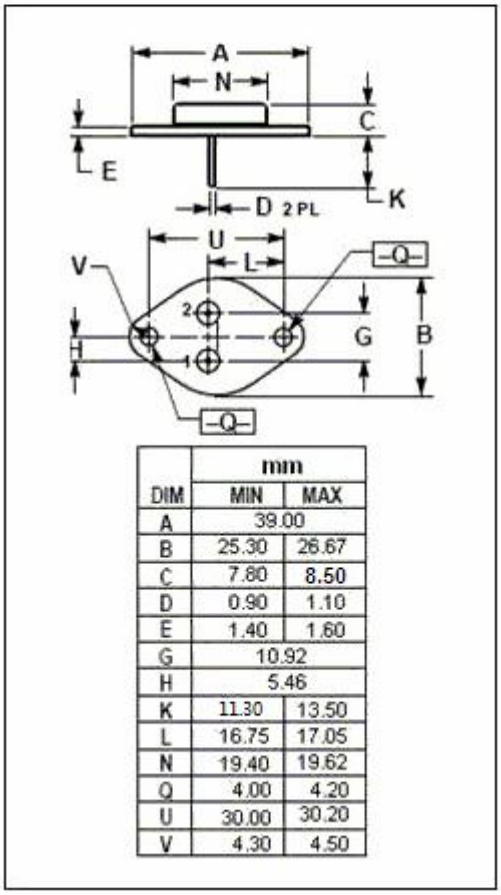


DESCRIPTION

- With TO-3 Package
- High Voltage Capability
- Low collector saturation voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation.

APPLICATIONS

- Designed for high voltage power switching TV horizontal deflection output applications.



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	600	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	1.5	A
I_{CM}	Collector Current-Peak	2	A
P_C	Collector Power Dissipation @ T_C=25℃	50	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-45-150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 10mA; I_C= 0	6		V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA; I_B= 0	600		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 1A; I_B= 0.2A		5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 1A; I_B= 0.2A		1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}=1500V;I_B= 0		0.5	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 6V; I_C=0		100	uA
h_{FE}	DC Current Gain	I_C= 1A ; V_{CE}= 5V	8	36	
t_f	Fall Time	I_C= 0.8A; I_{B1}= 0.16A; I_{B2}= 0.2A		1.5	μ s